Recent results and perspectives of the Monopix Depleted Monolithic Active Pixel Sensors (DMAPS)

M. Barbero⁴, P. Barrillon⁴, C. Bespin¹, P. Breugnon⁴, I. Caicedo¹, Y. Degerli³, J. Dingfelder¹, T. Hemperek¹, T. Hirono¹, F. Hügging¹, H. Krüger¹, K. Moustakas¹, P. Pangaud⁴, H. Pernegger², P. Riedler², P. Rymaszewski¹, L. Schall¹, P. Schwemling³, W. Snoeys², T. Wang¹, N. Wermes¹ and ⁵. Zhang¹ ¹Universität Bonn,²CERN, ³IRFU CEA-Saclay, ⁴CNRS/IN2P3 CPPM Marseille



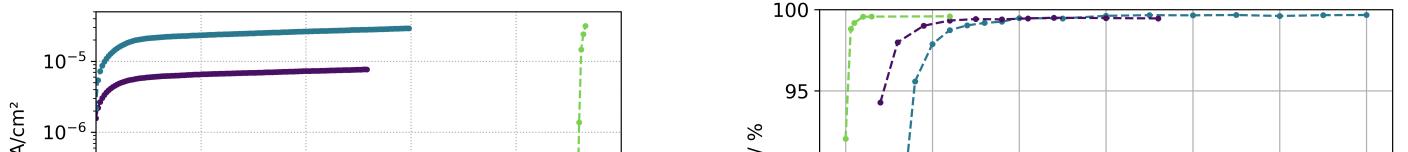
The Monopix design

The Monopix design implements monolithic active pixel detectors in commercial CMOS imaging technologies. High-resitivity substrates with high-voltage capabilities facilitate depletion of the charge-sensitive volume, maximizing the charge collection potential and enabling fast signal generation by drift.

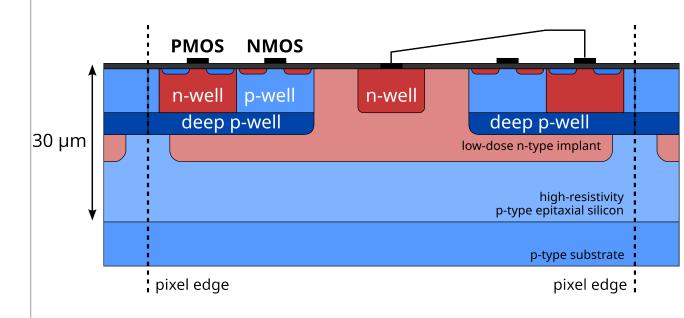
The presented prototypes, TJ-Monopix2 and LF-Monopix2, differ in the size of the readout electrode relative the pixel area. The small collection electrode approach (TJ-Monopix2) offers low analog power consumption and minimal noise operation due its low detector capacitance. Its sensor geometry has to be tuned carefully to achieve a significant radiation tolerance (> 10¹⁴ 1 MeV neq cm⁻²). A design with large collection electrode (LF-Monopix2) that houses all in-pixel readout electronics exhibits a larger radiation tolerance by default at the cost of a higher detector capacitance.

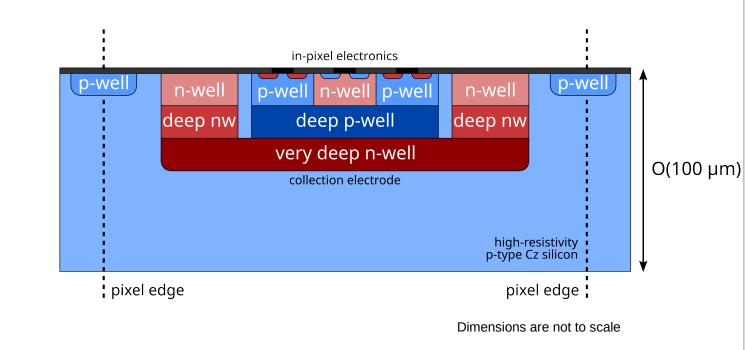
Radiation hardness

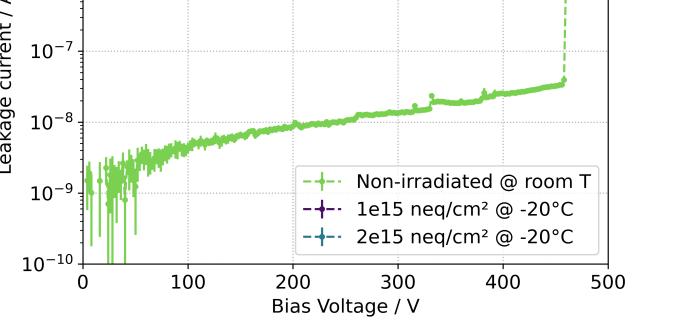
With dedicated design efforts, the breakdown voltage of LF-Monopix2 is increased to larger than 450 V before irradiation. The ENC increases from 90 e⁻ to 180 e⁻ after a NIEL fluence of 2 x 10¹⁵ neq cm⁻². Its large bias El voltage capabilities allow for hit detection efficiencies above 99 % at these NIEL fluence levels.

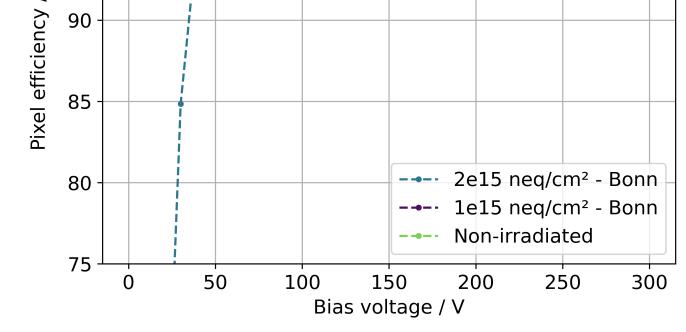


vn er	NIEL fluence [neq]	0	1 x 10 ¹⁵	2 x 10 ¹⁵
IC EL	Threshold [e⁻]	2040	2090	2070
as	ENC [e⁻]	87	120	178
on				







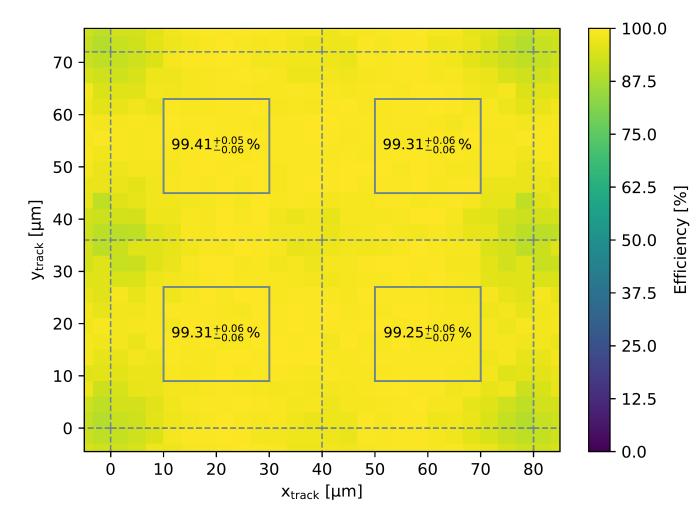


TJ-Monopix2:

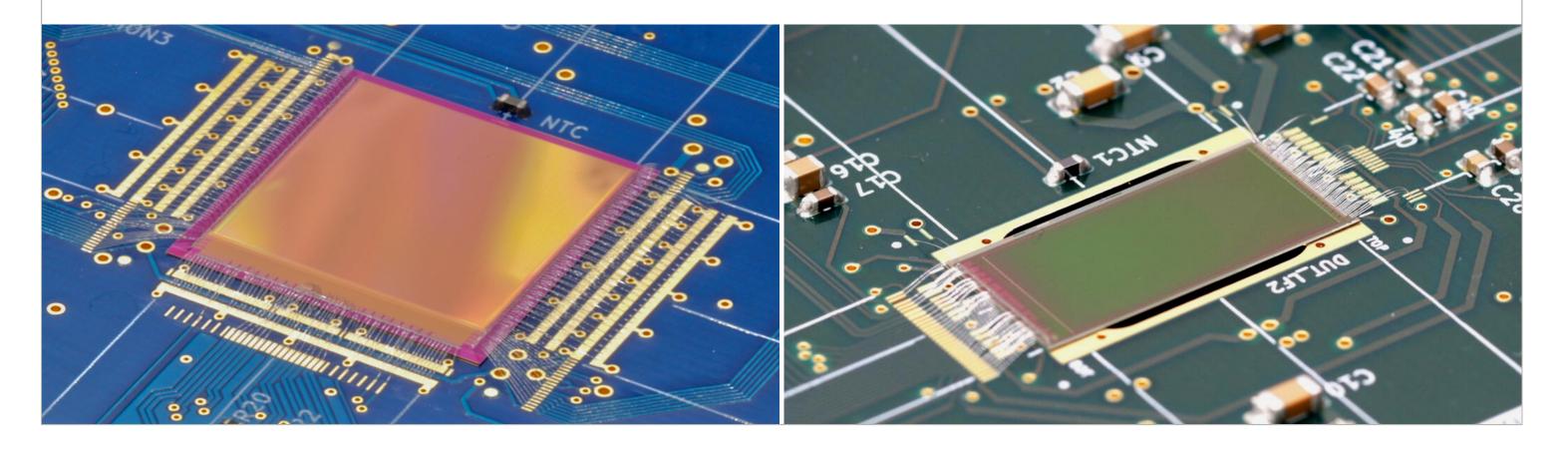
- 180 nm TowerSemi technology
- 512 x 512 pixels of 33 x 33 μm^2 each
- 7-bit ToT energy measurement @ 40 MHz
- 3-bit in-pixel tuning DAC
- O(2 fF) detector capacitance
- $1\,\mu W$ per pixel analog power

LF-Monopix2:

- 150 nm LFoundry technology
- 56 x 340 pixels of 150 x 50 μ m² each
- 6-bit ToT energy measurement @ 40 MHz
- 4-bit in-pixel tuning DAC
- O(250 fF) detector capacitance
- \bullet 28 μW per pixel analog power



In the TJ-Monopix design series, a modification has been developed together with the foundry to increase the radiation hardness of the small collection electrode design. In this geometry, hit detection efficiencies above 98 % could be achieved at a NIEL fluence of 1 x 10¹⁵ neq cm⁻². A lower detection threshold in TJ-Monopix2 is expected to reduce the losses in the pixel corners for a more homogeneous detection efficiency above 99 %.



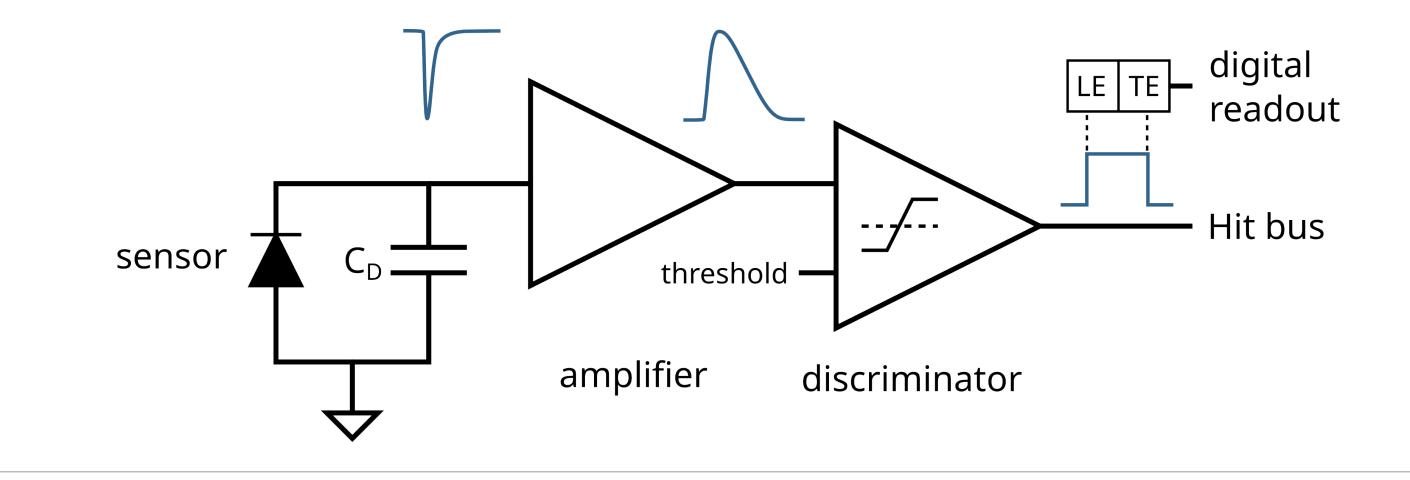
Timing performance

The amplifier implemented in TJ-Monopix2 facilitates fast detection of the deposited charge

Front-end working principle

According to V = Q / C, the front-end input signal in TJ-Monopix2 is considerably larger than in LF-Monopix2 and can be amplified with a single-stage voltage amplifier while LF-Monopix2 makes use of a conventional charge-sensitive amplifier.

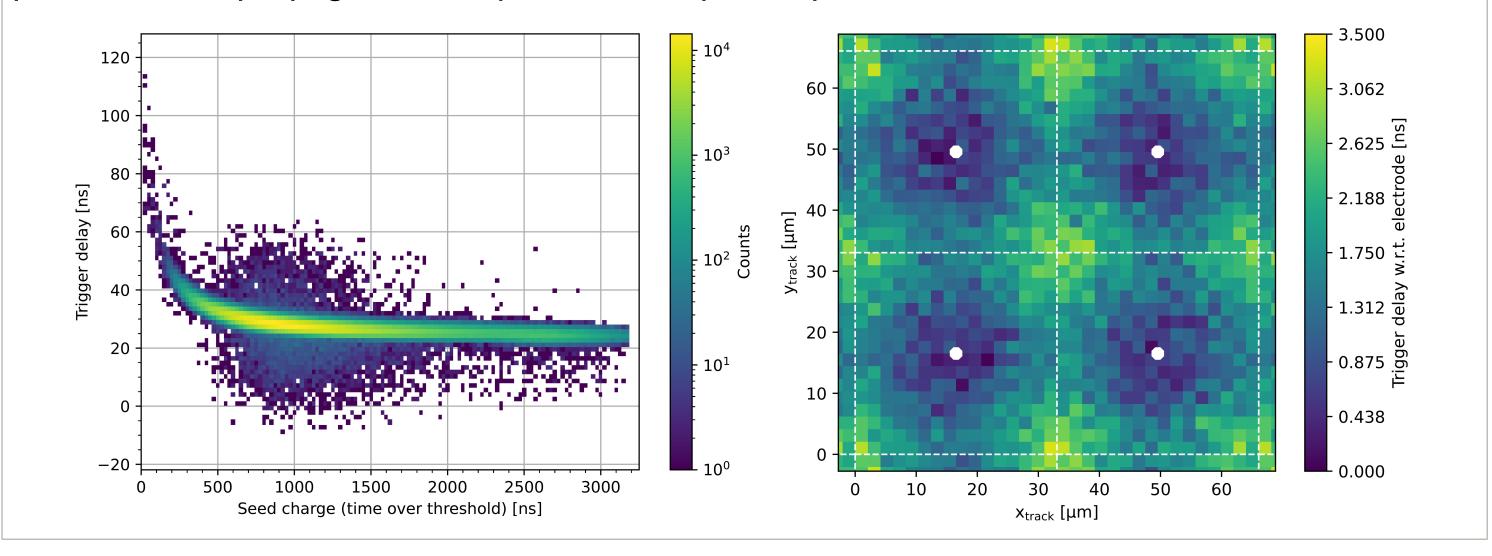
The matrix of both prototypes is read out using an established column-drain architecture derived from the FE-I3 readout chip.



Threshold response

Under typical operating conditions, the prototypes achieve a threshold response of 200 e⁻ and

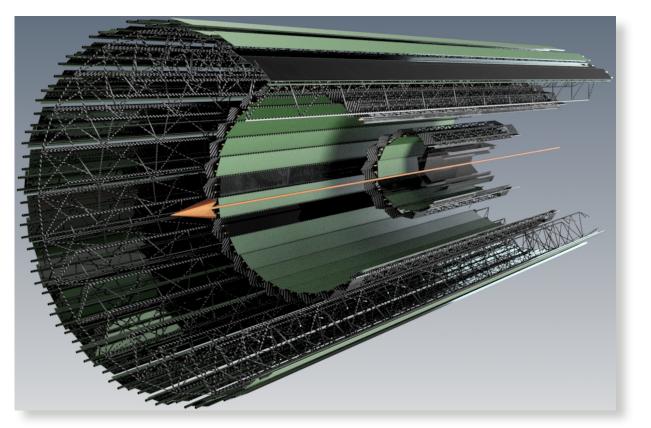
with a time resolution of less than 100 ps for charge values in the order of the most probable charge of minimally ionizing particles. Measurements in particle beams demonstrate a total time resolution of the pixel of about 1.3 ns (time walk corrected) which is dominated by physics processes and propagation delays within the pixel (up to 3 ns without time walk correction).



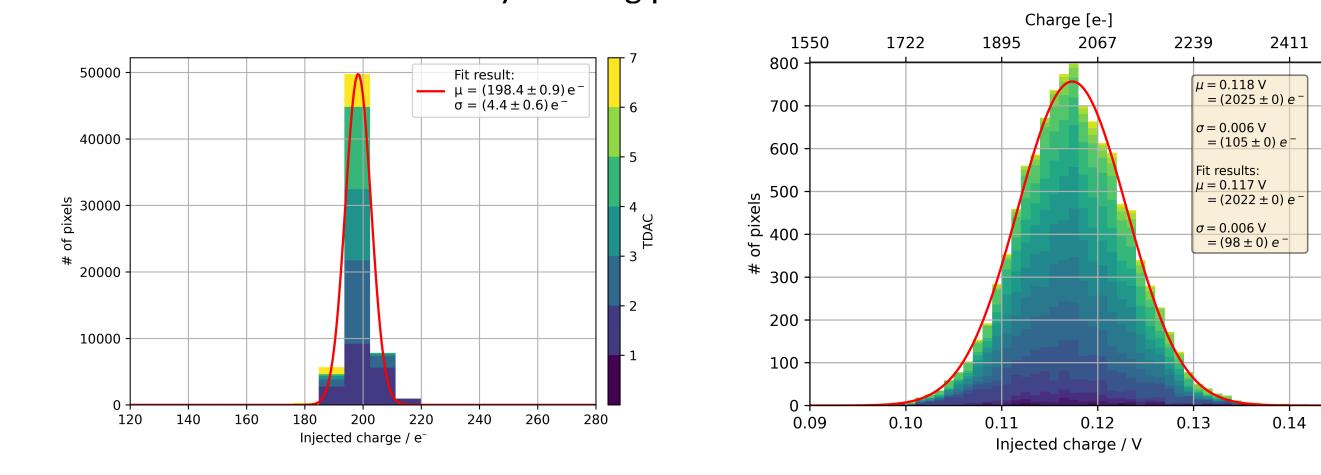
Conclusion & Outlook

Both presented depleted monolithic active pixel sensors demonstrate a good performance for high-radiation and high-rate environments in particle physics experiments. LF-Monopix2 exceeds its target radiation tolerance (1 x 10¹⁵ neq cm⁻²) with no significant degradation at the available NIEL fluences.

TJ-Monopix2 offers a high granularity and fast



2000 e⁻ for TJ-Monopix2 and LF-Monopix2, respectively, with most probable charge values of 2500 e⁻ and 6000 e⁻ for minimally ionizing particles.



LF-Monopix2 exhibits an equivalent noise charge (ENC) of approx. 100 e^- , while the small detector capacitance in TJ-Monopix2 is beneficial for noise levels as low as 5 e^- .

readout combined with a low power consumption. First results hint to an improved radiation tolerance compared to its predecessor. With its performance, it serves as a baseline for a future Belle II vertex detector in the same CMOS technology.

F. Forti Snowmass Whitepaper: The Belle II Detector Upgrade Program arXiv:2203.11349







+ 14

- 13

- 12

- 11

- 10

- 1